



Attorney's Docket No. 42P17814
Confirmation No.: 8503

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Robert Chau, et al.

Application No.: 10/760,028

Filed: January 16, 2004

For: TRI-GATE TRANSISTORS AND
METHODS TO FABRICATE SAME

Examiner: Smith, Bradley

Art Unit: 2891

Mail Stop Amendment
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Dianne Neathery

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Appl. No.: 10/760,028
Filing Date: January 16, 2004

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LJV/cak (10/27/04)
Atty. Docket: 42P17814

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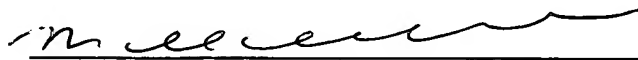
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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: May 9, 2006



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INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/760,028
Filing Date	January 16, 2004
First Named Inventor:	Robert Chau, et al.
Art Unit	2891
Examiner Name	Smith, Bradley
Attorney Docket No.:	42P17814

Sheet 1 of 4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		US-				
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NON PATENT LITERATURE DOCUMENTS

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		International Search Report PCT/US2005/035380, mailed 2/13/2006 (14 pgs.)	
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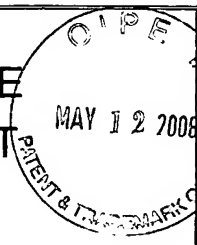
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